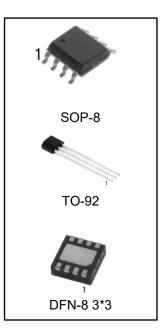


Description

The LM236 and LM336 are precision 2.5V regulator diodes. These voltage reference monolithic ICs operate like 2.5V zener diodes with a low temperature coefficient and a dynamic impedance of 0.2Ω . A third pin enables adjusting the reference voltage and the temperature coefficient.

Features

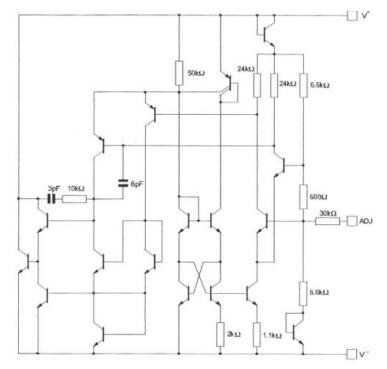
- Low temperature coefficient
- Wide operating current of 400µA to 10 mA
- 0.2Ω dynamic impedance
- ± 1% initial tolerance available
- Guaranteed temperature stability
- Fast turn-on



Ordering Information

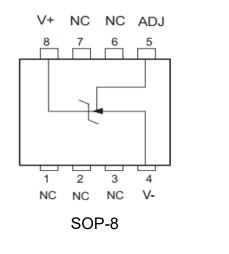
DEVICE	Package Type	MARKING	Packing	Packing Qty
LM236D-2.5RG	SOP-8	236-2.5	Reel	2500pcs/reel
LM336D-2.5RG	SOP-8	336-2.5	Reel	2500pcs/reel
LM236LP-2.5G	TO-92	LM236-2.5	Bag	1000pcs/box
LM336LP-2.5G	TO-92	LM336-2.5	Bag	1000pcs/box
LM236DQ-2.5RG	DFN-8 3*3	236-2.5	Reel	2500pcs/reel
LM336DQ-2.5RG	DFN-8 3*3	336-2.5	Reel	2500pcs/reel

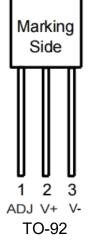
Schematic Diagram

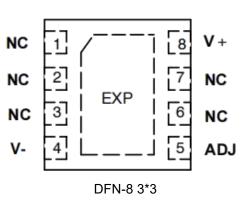




Pin Connections







Absolute Maximum Ratings

Symbol	Parameter	LM336	Unit
	Current		
IRIF	Reverse	15	mA
	Forward	10	
Toper	Operating Free-air Temperature Range	LM336-2.5: 0 to +70	°C
торег	Operating Tree-air Temperature Mange	LM236-2.5: -40 to +85	°C
T _{Stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (Soldering, 10 seconds)	245	°C

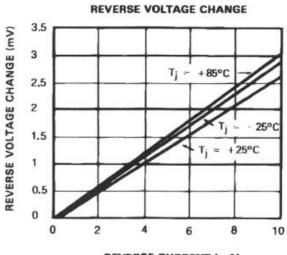
Note: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured.

Electrical Characteristics

Currence al	Denometer	LN	Unit		
Symbol	Parameter	Min.	Тур.	Max.	Unit
	Reference Breakdown Voltage				
VR	T_{amb} = +25°C, I_R = 1mA	2.44	2.49	2.54	V
	LM336				
	Reverse Breakdown Voltage Change with Current				
ΔVR	$400\mu A \le I_R \le 10m A$				
∆vR	T_{amb} = +25°C	-	2.6	10	mV
	T _{min.} ≤ T _{amb} ≤ T _{max.}		3	12	
	Reverse Dynamic Impedance (I _R = 1mA)				
ZD	$T_{amb} = +25^{\circ}C$	-	0.2	1	Ω
	T _{min.} ≤ T _{amb} ≤ T _{max.}		0.4	1.4	
KVT	Temperature Stability (V_R = 2.49V, I _R = 1mA)	-	1.8	6	mV
К _{VH}	Long Term Stability (T_{amb} = +25°C ±0.1°C, I_R = 1mA)	-	20	-	ppm

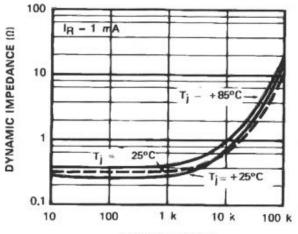


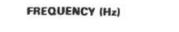
Typical Performance Characteristics

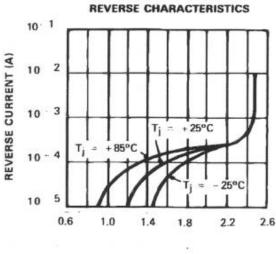


REVERSE CURRENT (mA)

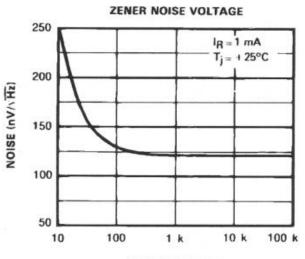






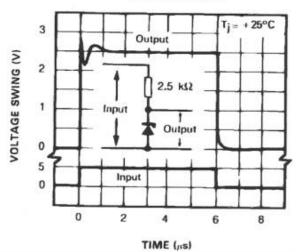


REVERSE VOLTAGE (V)

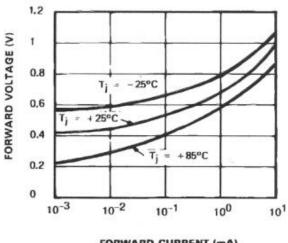


FREQUENCY (Hz)





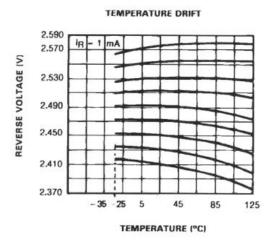




FORWARD CURRENT (mA)



Typical Performance Characteristics (Continued)

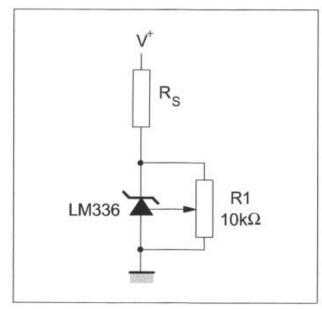


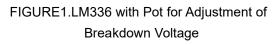
Application Hints

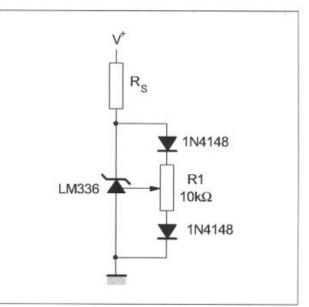
The LM336 voltage references are easier to use than zener diodes. Their low impedance and wide current range facilitate biasing in any circuits. Besides, the breakdown voltage or the temperature coefficient can be adjusted so as to optimize the performance of the circuit.

Figure 1 represents a LM336 with a $10k\Omega$ potentiometer to adjust the reverse breakdown voltage which can be adjusted without altering the temperature coefficient of the circuit. The adjustment range is generally sufficient to adjust the initial tolerance of the circuit and the inaccuracy of the amplifier circuit.

To obtain a lower temperature coefficient two diodes can be connected in series as indicated in Figure 2. When the circuit is adjusted to 2.49V the temperature coefficient is minimized. For a correct temperature coefficient, the diodes should be at the same ambient temperature as the LM336. The value of R1 is not critical (2-20k Ω).







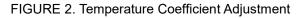
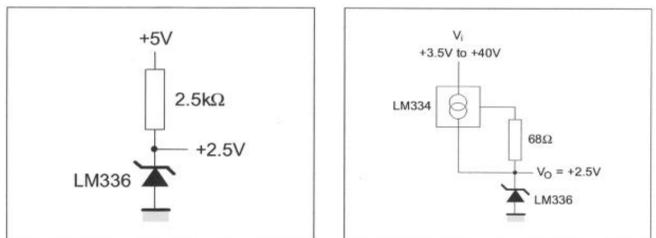


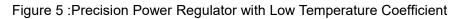


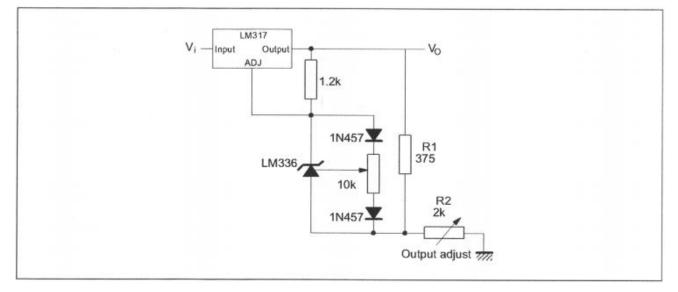
Figure 4 :Wide Input Range Reference

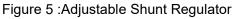
Typical Applications

Figure 3 :2.5V Reference









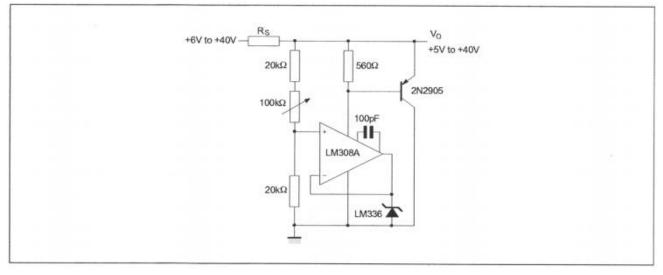




Figure 7 :Linear Ohmmeter

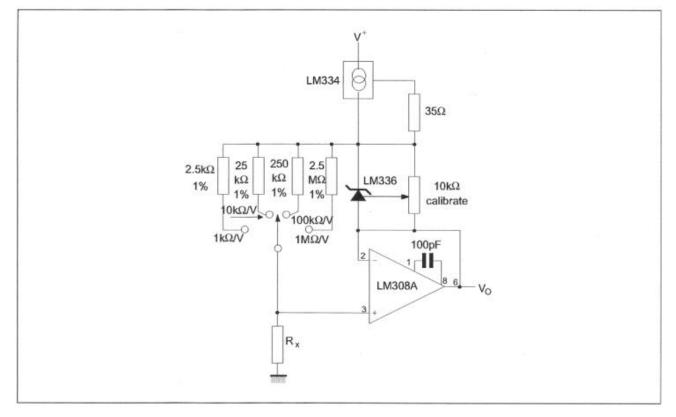


Figure 8 :Bipolar Output Reference

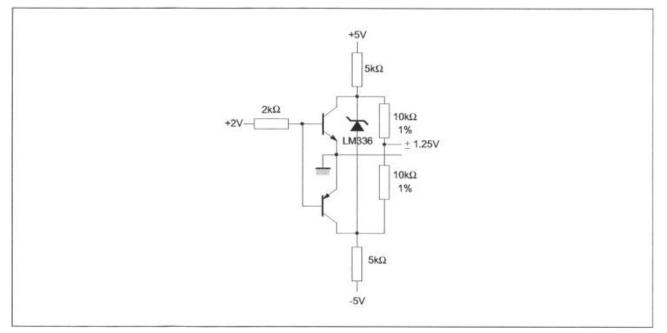




Figure 9 : 5V Buffered Reference

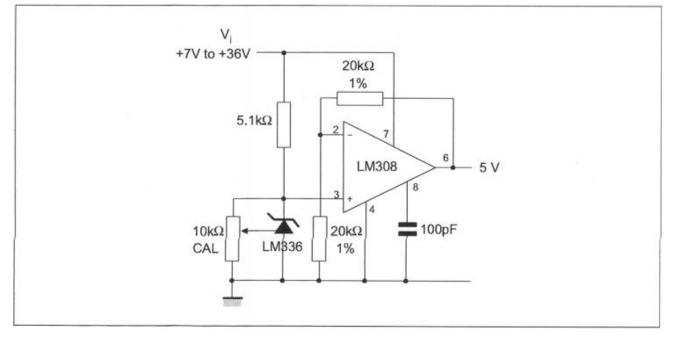
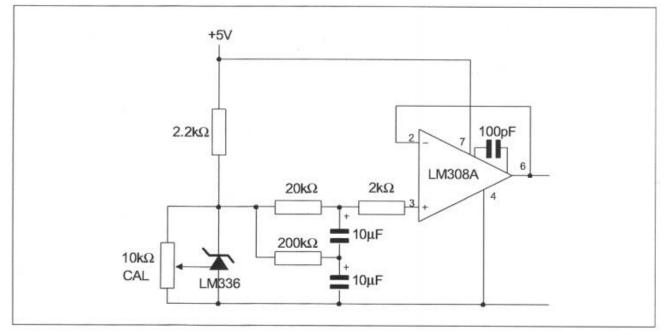


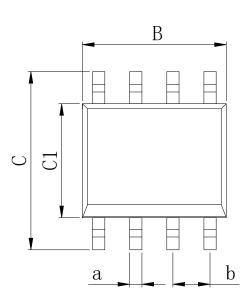
Figure 10 : Low Noise Buffered Reference

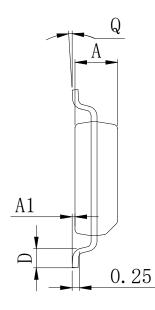




Physical Dimensions

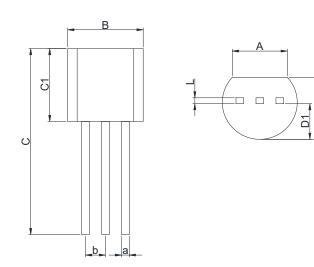
SOP-8





Dimensions In Millimeters(SOP-8)									
Symbol:	А	A1	В	С	C1	D	Q	а	b
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	4.07.000
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	1.27 BSC

TO-92

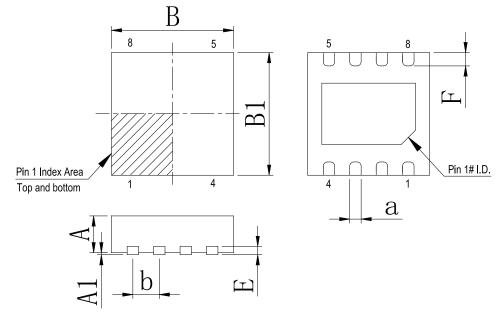


Dimensions In Millimeters(TO-92)									
Symbol:	A	В	С	C1	D	D1	L	а	b
Min:	3.43	4.44	11.2	4.32	3.17	2.03	0.33	0.40	4.07000
Max:	3.83	5.21	12.7	5.34	4.19	2.67	0.42	0.52	1.27BSC



Physical Dimensions

DFN-8 3*3



Dimensions In Millimeters(DFN-8 3*3)									
Symbol:	А	A1	В	B1	Е	F	а	b	
Min:	0.85	0.00	2.90	2.90	0.20	0.30	0.20		
Max:	0.95	0.05	3.10	3.10	0.25	0.50	0.34	0.65 BSC	



Revision History

DATE	REVISION	PAGE
2018-9-5	New	1-11
2023-9-13	Update Lead Temperature、Add annotation for Maximum Ratings.	2



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